

Abstract of the Disclosure

5 A high power RF amplifier utilizes dynamic biasing for transistors in an
output stage of the amplifier. In one embodiment, as the magnitude of an RF signal
to be amplified falls below a predetermined level, the biasing signal is turned off to
reduce power consumption. A gate bias voltage is used to switch the transistors off
and on. A low pass filter is employed to eliminate noise generated at the output of the
amplifier caused by the instantaneous switching, while not impacting the amplifier's
response to low-high magnitude transients. In a further embodiment, I and Q data
10 from baseband digital data is sampled and buffered prior to being transformed and
provided to a RF power amplifier. A gate bias signal is controlled based on current
samples in order to control the power amplifier in a manner appropriate for the current
samples when provided from the buffer.

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